

THE COMMISSIONER IS AUTHORIZED TO CHARGE ANY DEFICIENCY IN THE FEES FOR THIS PAPER TO DEPOSIT ACCOUNT NO. 23-0975

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Mitsuhiro OKUNE et al.

: Mail Stop: PCT

Serial No. 10/581,256

Attorney Docket No. 2006_0772A

Filed May 31, 2006

PLASMA ETCHING METHOD [Corresponding to PCT/JP2004/017622 Filed November 26, 2004]

SUBMISSION OF ENGLISH VERSIONS OF INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY AND WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Submitted herewith for consideration by the Examiner are:

- 1) An English version of the International Preliminary Report on Patentability; and
- 2) An English version of the Written Opinion of the International Searching

Authority.

Respectfully submitted,

Mitsuhiro OKUNE et al.

Charles R. Watts

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PATENT COOPERATION TREATY

From the INTERNATIONAL BUREAU

PCT

NOTIFICATION OF TRANSMITTAL
OF COPIES OF TRANSLATION
OF THE INTERNATIONAL PRELIMINARY REPORT
ON PATENTABILITY
(CHAPTER I OR CHAPTER II
OF THE PATENT COOPERATION TREATY)

(PCT Rules 44bis.3(c) and 72.2)

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v.

NII, Hiromori c/o NII Patent Firm 6F, Tanaka Ito Pia Shin-Osaka Bldg. 3-10, Nishi Nakajima 5-chome Yodogawa-ku, Osaka-city Osaka 532-0011 JAPON

06, 9,12

Date of mailing (day/month/year) 31 August 2006 (31.08.2006)	SECELO SECTION DE LA COMPANION
Applicant's or agent's file reference P37020-P0	IMPORTANT NOTIFICATION
International application No. PCT/JP2004/017622	International filing date (day/month/year) 26 November 2004 (26.11.2004)
Applicant MATSUSHITA	ELECTRIC INDUSTRIAL CO., LTD. et al

ı	Transmittal of	the	translation	to	the applicant.
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7	The International Bureau transmits herewith a copy of the English translation of the international preliminary report of
j	patentability (Chapter I).

The International Bureau transmits herewith a copy of the English translation of the international preliminary report on patentability (Chapter II).

2. Transmittal of the copy of the translation to the designated or elected Offices.

The International Bureau notifies the applicant that copies of that translation have been transmitted to the following designated or elected Offices requiring such translation:

EP, KR

The following designated or elected Offices, having waived the requirement for such a transmittal at this time, will receive copies of that translation from the International Bureau only upon their request:

AE, AG, AL, AM, AP, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EA, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OA, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW

3. Reminder regarding translation into (one of) the official language(s) of the elected Office(s).

The applicant is reminded that, where a translation of the international application must be furnished to an elected Office, that translation must contain a translation of any annexes to the international preliminary report on patentability (Chapter II).

It is the applicant's responsibility to prepare and furnish such translation directly to each elected Office concerned within the applicable time limit (Rule 74.1). See Volume II of the PCT Applicant's Guide for further details.

The International Bureau of WIPO 34, chemin des Colombettes 1211-Geneva-20,-Switzerland	Authorized officer Yoshiko Kuwahara
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PATENT COOPERATION TREATY

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TRANSLATION INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

(Chapter II of the Patent Cooperation Treaty)

(PCT Article 36 and Rule 70)

Applicant's or agent's file reference P37020-P0	FOR FURTHER ACTION	See Form PCT/IPEA/416						
International application No.	International filing date (day/month/year	r) Priority date (day/month/year)						
PCT/JP2004/017622	26.11.2004	01.12.2003						
nternational Patent Classification (IPC H01L21/3065 Applicant . MATSUSHITA ELECTE	C) or national classification and IPC RIC INDUSTRIAL CO., LTD	•						
	tted to the applicant according to Article 36.	this International Preliminary Examining Authority						
	ied by ANNEXES, comprising:							
	cant and to the International Bureau) a total of							
		sheets, as follows: been amended and are the basis for this report and/or						
	ining rectifications authorized by this Authority (s	see Rule 70.16 and Section 607 of the Administrative						
	•	y considers contain an amendment that goes beyond icated in item 4 of Box No. I and the Supplemental						
	ational Pursay only) a total of (indicate type and	weeker of alcotronic consists (s)						
o (sent to the theen	national Bureau only) a total of (indicate type and n							
	omputer readable form only, as indicated in the S	containing a sequence listing and/or tables applemental Box Relating to Sequence Listing (see						
4. This report contains indicatio	ns relating to the following items:							
Box No. I Bas	is of the report							
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$\overline{\Box}$	rity	and the state and the desirable to the Color						
	n-establishment of opinion with regard to novelty, i	nvenuve step and industrial applicability						
	k of unity of invention	and the formation and the second seco						
DOX NO. V	soned statement under Article 35(2) with regard to tions and explanations supporting such statement	noveny, inventive step or industrial applicability;						
Box No. VI Cert	ain documents cited							
Box No. VII Certain defects in the international application								
Box No. VIII Certain observations on the international application								
ate of submission of the demand	Date of completion	of this report						
are or submission of the demand	Date of completion	or this report						
ame and mailing address of the IPEA	JP Authorized officer	Authorized officer						
acsimile No.	Telephone No.							

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No.

PCT/JP2004/017622

Во	x No. I	I	Basis of the report							
1.			I to the language, this report is based on the internation	onal application in the language i	n which it was filed, unless otherwise					
		This report is based on translations from the original language into the following language which is the language of a translation furnished for the purposes of:								
		international search (Rule 12.3 and 23.1(b))								
		publication of the international application (Rule 12.4)								
			international preliminary examination (Rule 55.2 and	/or 55.3)						
2.	rece		to the elements of the international application, this ffice in response to an invitation under Article 14 and							
		the int	ernational application as originally filed/furnished							
	\bowtie	the de	scription:							
		pages	1-16		as originally filed/furnished					
		pages'	<u> </u>	received by this Authority on						
		pages'	<u> </u>	received by this Authority on						
	\boxtimes	the cla	úms:							
		nos.	2-8,10-12,14,16-19		as originally filed/furnished					
		nos.*		as amended (togeth	er with any statement) under Article 19					
		nos.*	1,9,15	received by this Authority on	29.09.2005					
		nos.*								
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	\square	-	ence listing and/or any related table(s) – see Supplement	ental Box Relating to Sequence 1	arsung.					
3.			nendments have resulted in the cancellation of:							
		\square	he description, pages		<u> </u>					
			he claims, nos. 13							
			he sequence listing (specify):							
		∐ a	ny table(s) related to sequence listing (specify):							
4.										
			port has been established as if (some of) the amendative been considered to go beyond the disclosure as file.							
		they ha		ed, as indicated in the Supplemen	ntal Box (Rule 70.2(c)).					
		they ha	we been considered to go beyond the disclosure as file	ed, as indicated in the Supplemen	ntal Box (Rule 70.2(c)).					
		they ha	we been considered to go beyond the disclosure as file the description, pages	ed, as indicated in the Supplemen	ntal Box (Rule 70.2(c)).					
		they ha	we been considered to go beyond the disclosure as file the description, pages the claims, nos. the drawings, sheets/figs	ed, as indicated in the Supplemen	ntal Box (Rule 70.2(c)).					
		they had	we been considered to go beyond the disclosure as file the description, pages the claims, nos. the drawings, sheets/figs	ed, as indicated in the Supplemen	ntal Box (Rule 70.2(c)).					

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No.
PCT/JP2004/017622

Box	Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement						
1.	Statement						· · · · · · · · · · · · · · · · · · ·
	Novelty (N)	(Claims	1-12,	14-1	9	YES
		(Claims				NO
	Inventive ste	ep (IS)	Claims				YES
		(Claims	1-12,	14-1	9	NO
	Industrial ap	plicability (IA)	Claims	1-12,	14-19	9	YES
		(Claims				NO

2. Citations and explanations (Rule 70.7)

The following documents are cited in the international search report.

- Document 1: JP 2002-542623 A (Lam Research Corp.), 10

 December 2002, paragraphs [0026] to [0033]
- Document 2: JP 2003-303812 A (Matsushita Electric Industrial Co., Ltd.), 24 October 2003, paragraph [0094] and fig. 1
- Document 3: JP 2000-299310 A (Denso Corp.), 24 October 2000, paragraphs [0063] to [0072] and fig. 7
- Document 4: WO 2003-030239 Al (Sumitomo Precision Products Co., Ltd.), 10 April 2003, paragraph [0094] and fig. 1
- Document 5: JP 2001-284283 A (Hitachi, Ltd.), 12 October 2001, paragraph [0098]

Claims 1 to 10, 18 and 19

Document 1 discloses a method for plasma etching a silicon object within a processing chamber, wherein trenches are formed in the aforementioned silicon object by introducing an etching gas that contains O_2 , SF_6 , He or Cl_2 into the interior of the aforementioned processing chamber and then converting the aforementioned etching

Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

gas into a plasma by means of a TCP device.

Meanwhile, document 2 indicates that high-frequency power with a frequency in the range of 50 kHz to 500 MHz is applied to the coil of the TCP device. Such being the case, it would have been obvious to a person skilled in the art to configure so that high-frequency power with a frequency in the range of 50 kHz to 500 MHz is applied to the coil of the TCP device in the invention disclosed in document 1.

Furthermore, a person skilled in the art could set an appropriate frequency for the high-frequency power, regardless of the type of plasma etching gas that is used.

Such being the case, the inventions set forth in claims 1 to 10, 18 and 19 do not involve an inventive step.

Claims 11, 12 and 14

Document 1 discloses a method for plasma etching a silicon object within a processing chamber, wherein trenches are formed in the aforementioned silicon object by introducing an etching gas that contains O_2 , SF_6 , He or Cl_2 into the interior of the aforementioned processing chamber and then converting the aforementioned etching gas into a plasma by means of a TCP device.

Meanwhile, document 2 indicates that high-frequency power with a frequency in the range of 50 kHz to 500 MHz is applied to the coil of the TCP device.

Furthermore, document 3 discloses a trench formation method wherein trenches are formed by means of SF₆ gas, and then a protective film is formed upon the side walls of the trenches-by-means-of-a-gas that

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Box No. V

Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

contains C₄F*.

In addition, document 4 discloses a feature wherein trenches are formed by means of a gas system that contains SF_6 and C_4F_8 , which is a gas for forming a protective film.

Documents 1, 3 and 4 all pertain to the same technical feature; i.e., forming trenches on a silicon substrate. Therefore, it is considered to have been easy for a person skilled in the art to conceive of forming trenches by means of the gas disclosed in document 1, which contains O_2 , SF_6 , He or Cl_2 , and then forming both trenches and protective films by means of the gas system disclosed in document 4, which contains SF_6 and C_4F_8 , in the light of the disclosures in document 3.

Furthermore, in the light of the disclosure in document 2 it would have been obvious to a person skilled in the art to configure so that high-frequency power with a frequency in the range of 50 kHz to 500 MHz is applied to the coil of the TCP device in the invention disclosed in document 1.

Such being the case, the inventions set forth in claims 11, 12 and 14 do not involve an inventive step.

Claims 15 to 17

Document 5 discloses a method for plasma etching a silicon object by means of Ar/CF_4 . Therein, it would have been easy for a person skilled in the art to conceive of increasing the precision of the etching depth by adjusting the flow rate of the Ar or the CF_4 and by using a gas other than CF_4 in order to decrease the etching speed.

-Such-being-the-case,-the-inventions-set forth-in-

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No.
PCT/JP2004/017622

Box No. V	Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability: citations and explanations supporting such statement								or industrial applicability;
claims								inventive	step.
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